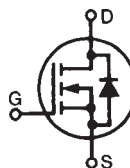


PolarHV™ HiPerFET IXFP7N80PM

Power MOSFET

(Electrically Isolated Tab)

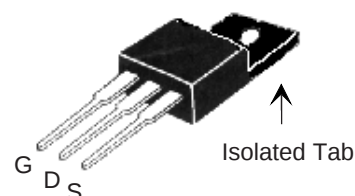
N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode



$$\begin{aligned} V_{DSS} &= 800 \text{ V} \\ I_{D25} &= 3.5 \text{ A} \\ R_{DS(on)} &\leq 1.44 \text{ } \Omega \\ t_{rr} &\leq 250 \text{ ns} \end{aligned}$$

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	800	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1 \text{ M}\Omega$	800	V
V_{GSS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ\text{C}$	3.5	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	18	A
I_{AR}	$T_C = 25^\circ\text{C}$	4	A
E_{AR}	$T_C = 25^\circ\text{C}$	20	mJ
E_{AS}	$T_C = 25^\circ\text{C}$	300	mJ
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 10 \text{ } \Omega$	10	V/ns
P_D	$T_C = 25^\circ\text{C}$	50	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$
T_{SOLD}	Plastic body for 10 s	260	$^\circ\text{C}$
M_d	Mounting torque	1.13/10	Nm/lb.in.
Weight		3.0	g

OVERMOLDED TO-220
(IXTP...M) OUTLINE



G = Gate D = Drain
S = Source

Features

- Plastic overmolded tab for electrical isolation
- Fast intrinsic diode
- International standard package
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
 - easy to drive and to protect

Advantages

- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 250 \text{ } \mu\text{A}$	800		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 1 \text{ mA}$	3.0		5.0 V
I_{GSS}	$V_{GS} = \pm 30 \text{ V}$, $V_{DS} = 0 \text{ V}$			$\pm 100 \text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$			25 μA
	$V_{GS} = 0 \text{ V}$ $T_J = 125^\circ\text{C}$			500 μA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$, $I_D = 3.5 \text{ A}$ Note 1			1.44 Ω

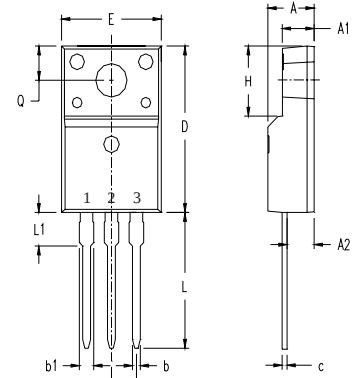
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 20\text{ V}$; $I_D = 3.5\text{ A}$, Note 1	5	9.5	S
C_{iss}	$V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$		1890	pF
C_{oss}			133	pF
C_{rss}			13	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}$, $V_{DS} = 0.5 V_{DSS}$, $I_D = 4\text{ A}$ $R_G = 10\ \Omega$ (External)		28	ns
t_r			32	ns
$t_{d(off)}$			55	ns
t_f			24	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}$, $V_{DS} = 0.5 V_{DSS}$, $I_D = 6\text{ A}$		32	nC
Q_{gs}			12	nC
Q_{gd}			9	nC
R_{thJC}				2.5 $^\circ\text{C/W}$

Source-Drain Diode

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$ unless otherwise specified)		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{ V}$			7 A
I_{SM}	Repetitive			18 A
V_{SD}	$I_F = I_S$, $V_{GS} = 0\text{ V}$, Note 1			1.5 V
t_{rr}	$I_F = 7\text{ A}$, $-di/dt = 100\text{ A}/\mu\text{s}$, $V_R = 100\text{ V}$, $V_{GS} = 0\text{ V}$	0.3	3	250 ns
Q_{RM}				μC
I_{RM}				A

Notes: 1) Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$

ISOLATED TO-220 (IXFP...M)



Terminals: 1 - Gate
2 - Drain (Collector)
3 - Source (Emitter)

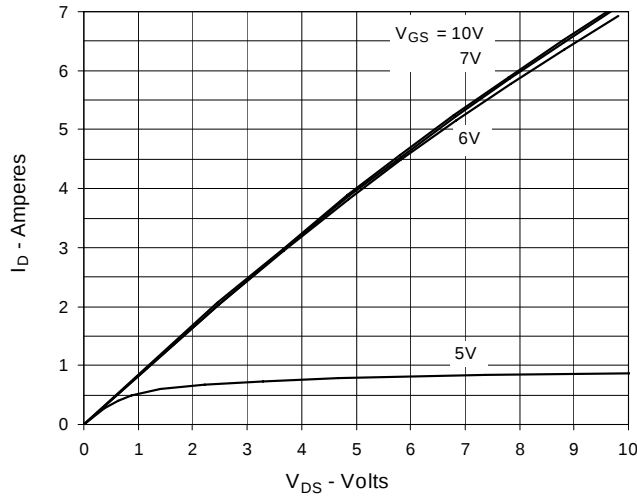
SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.177	.193	4.50	4.90
A1	.092	.108	2.34	2.74
A2	.101	.117	2.56	2.96
b	.028	.035	0.70	0.90
b1	.050	.058	1.27	1.47
c	.018	.024	0.45	0.60
D	.617	.633	15.67	16.07
E	.392	.408	9.96	10.36
e	.100 BSC		2.54 BSC	
H	.255	.271	6.48	6.88
L	.499	.523	12.68	13.28
L1	.119	.135	3.03	3.43
ØP	.121	.129	3.08	3.28
Q	.126	.134	3.20	3.40

IXYS reserves the right to change limits, test conditions, and dimensions.

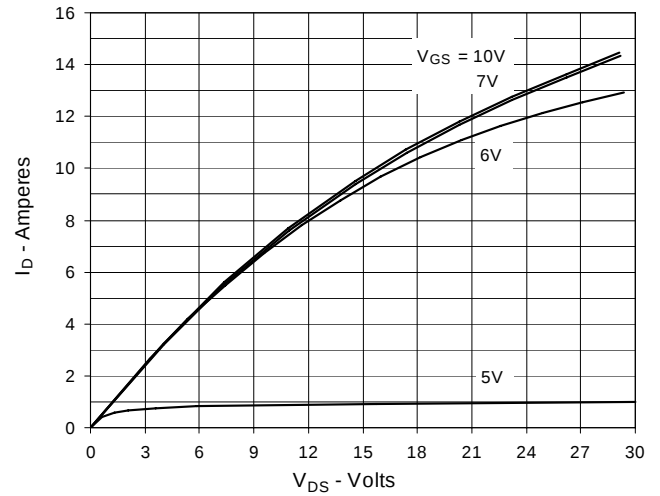
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2
4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537

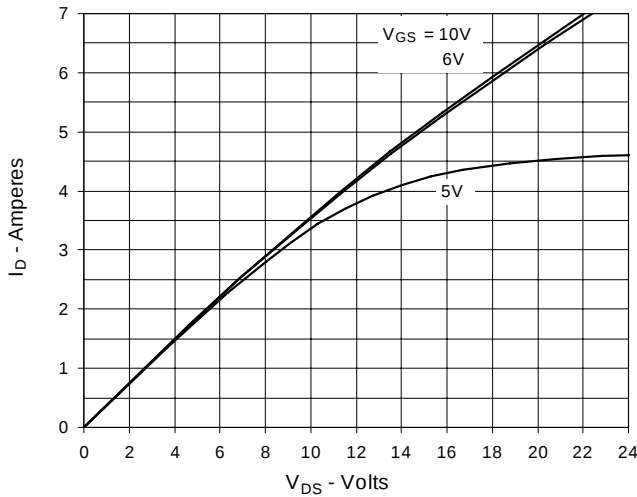
**Fig. 1. Output Characteristics
@ 25°C**



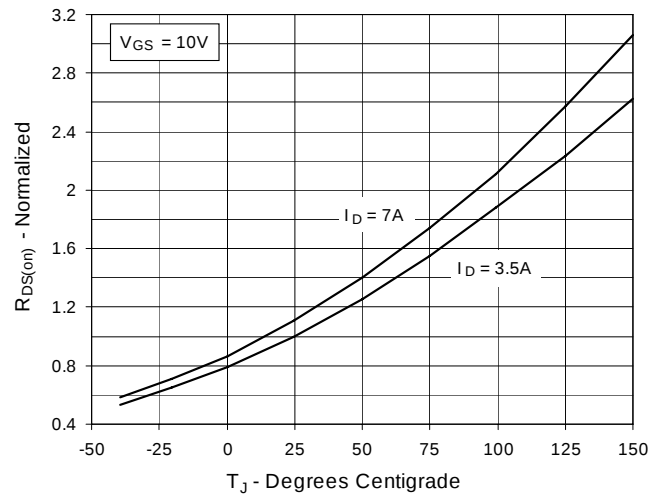
**Fig. 2. Extended Output Characteristics
@ 25°C**



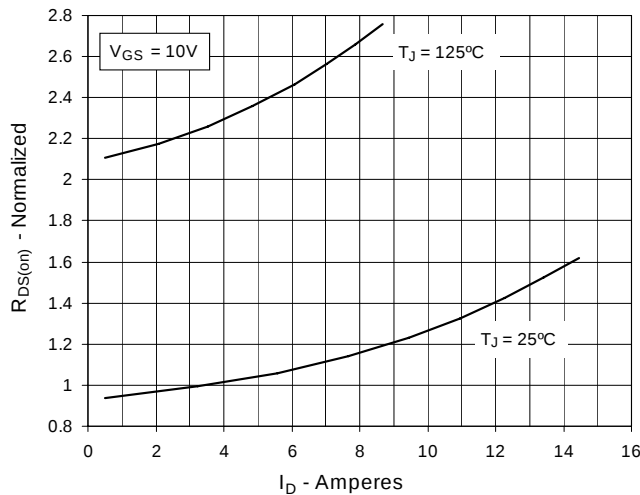
**Fig. 3. Output Characteristics
@ 125°C**



**Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 3.5A$ Value
vs. Junction Temperature**



**Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 3.5A$ Value
vs. Drain Current**



**Fig. 6. Maximum Drain Current vs.
Case Temperature**

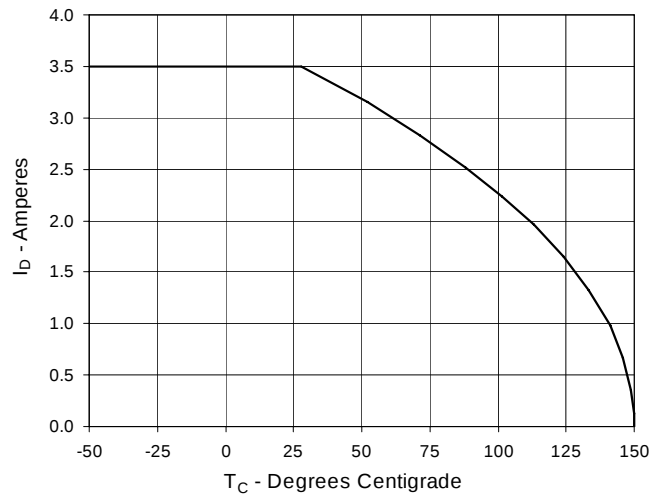


Fig. 7. Input Admittance

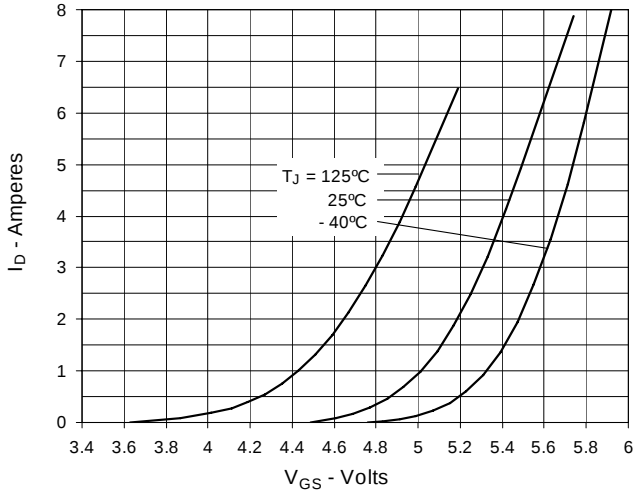


Fig. 8. Transconductance

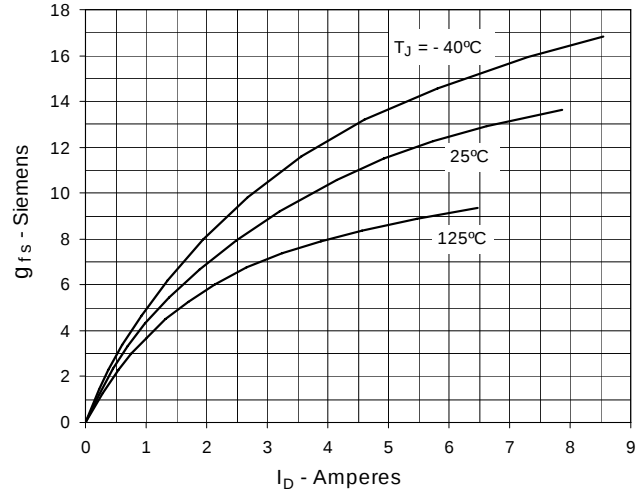


Fig. 9. Forward Voltage Drop of Intrinsic Diode

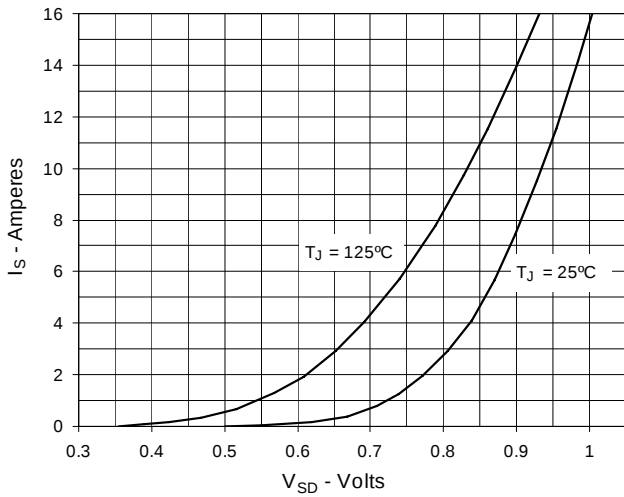


Fig. 10. Gate Charge

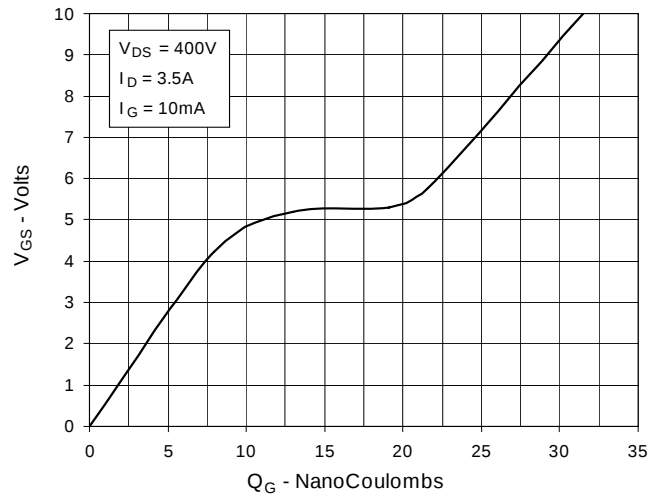


Fig. 11. Capacitance

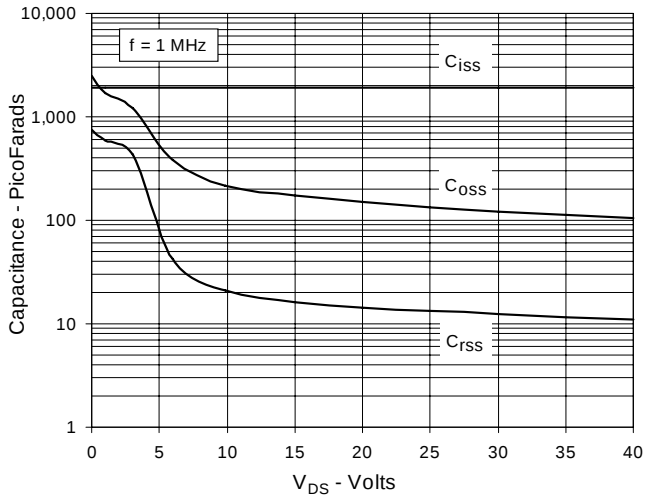


Fig. 12. Maximum Transient Thermal Resistance

